

A semiconductor component and a method of manufacturing it are described, making it possible to provide a switching element for high switching frequencies without the omnipresent leakage inductance resulting in high interference voltage peaks. Therefore, pits are produced in the surface of the wafer, resulting in a middle zone [(10)] having a variable thickness laterally. First areas [(40)] of this middle zone [(10)] guarantee a gentle drop in clearing current, second areas [(50)] guarantee short switching times and a low forward voltage.

(Figure 3a)